Silicon NPN Darlington Power Transistors 2SD2557

DESCRIPTION

・With TO-3PN package
・DARLINGTON

APPLICATIONS

・Series regulator and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

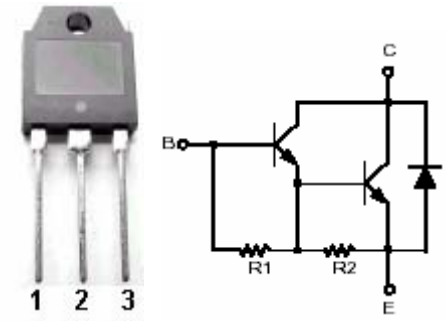

Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		5	A
I_B	Base current		2	A
P_C	Collector power dissipation	T_C=25℃	70	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA ;I_B=0	200			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=1A ;I_B=5mA			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=200V; I_E=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			5	mA
h_{FE}	DC current gain	I_C=1A ; V_{CE}=5V	1500		6500	
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=10V;f=1MHz		110		pF
f_T	Transition frequency	I_E=0.5A ; V_{CE}=10V		15		MHz

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PACKAGE OUTLINE

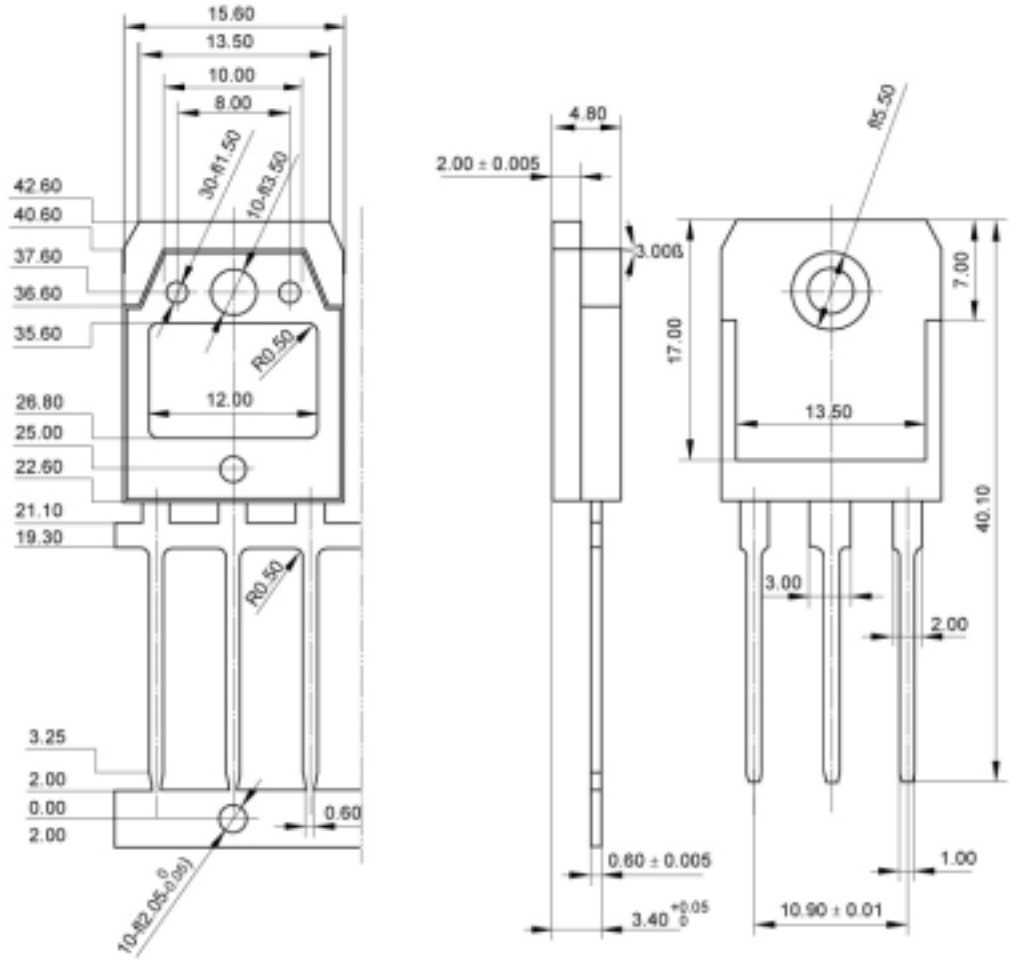

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)